

**Amendments To The Claims**

The following listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

Claims 1-26 (canceled)

Claim 27 (currently amended): A device comprising:

a substrate;

a lanthanum nickel ~~oxide~~ oxide ( $\text{LaNiO}_3$ ) layer formed over the substrate, said lanthanum nickel oxide layer having a non-amorphous microstructure that comprises grains of crystalline material, the grains having an average diameter in the range from 100 Å to 300 Å; and

a layer of ferro-electric material formed over said lanthanum nickel oxide layer.

Claim 28 (canceled).

Claim 29 (currently amended): The device of Claim 27 wherein the lanthanum nickel ~~oxide~~ oxide layer has an average surface roughness in a range from 2 nm to 3 nm.

Claim 30 (currently amended): The device of Claim 27 wherein the lanthanum nickel ~~oxide~~ oxide layer has a resistivity of less than  $330 \mu\Omega\cdot\text{cm}$ .

Claim 31 (currently amended): The device of Claim 27 wherein the lanthanum nickel ~~oxide~~ oxide layer has a resistivity of less than  $300 \mu\Omega\cdot\text{cm}$ .

Claim 32 (currently amended): The device of Claim 27 wherein the lanthanum nickel ~~oxide~~ oxide layer has a resistivity of less than  $250 \mu\Omega\cdot\text{cm}$ .

Claim 33 (New): The device of Claim 27 wherein the grains of the crystalline material of the lanthanum nickel oxide layer have a crystal lattice constant that is closely matched to the crystal lattice constant of the substrate.